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(54) **CHEMICALLY AMPLIFIED NEGATIVE
RESIST COMPOSITION AND RESIST
PATTERN FORMING PROCESS**

USPC 430/270.1, 905, 910; 562/100, 113;
568/34, 35
See application file for complete search history.

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This patent is subject to a terminal dis-
claimer.

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(57) **ABSTRACT**

A negative resist composition comprising a sulfonium com-
pound having formula (A) and a base polymer is provided.
The resist composition exhibits a high resolution during
pattern formation and forms a pattern with minimal LER.

(A)

